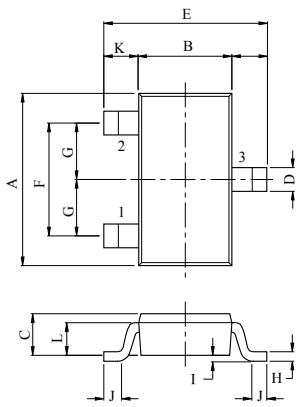
RELAY DRIVERS, LAMP DRIVERS,
MOTOR DRIVERS APPLICATION.

FEATURES

- Adoption of MBIT Processes.
- Large Current Capacitance.
- Low Collector-to-Emitter Saturation Voltage.
- High-Speed Switching.
- Ultrasmall Package Facilitates Miniaturization in end Products.
- High Allowable Power Dissipation.
- Complementary to KTA1532T



DIM	MILLIMETERS
A	2.9±0.2
B	1.6+0.2/-0.1
C	0.70±0.05
D	0.4±0.1
E	2.8+0.2/-0.3
F	1.9±0.2
G	0.95
H	0.16±0.05
I	0.00-0.10
J	0.25+0.25/-0.15
K	0.60
L	0.55

1. EMITTER
2. BASE
3. COLLECTOR

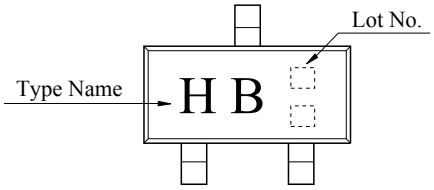
TSM

MAXIMUM RATING (Ta=25℃)

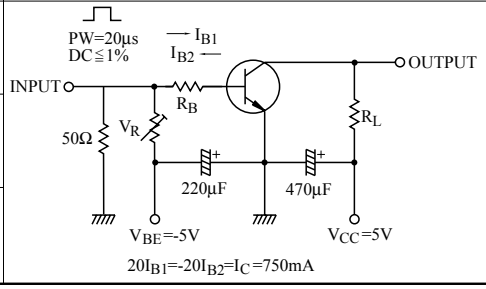
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	20	V
Collector-Emitter Voltage		V_{CEO}	20	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	1.5	A
	Pulse	I_{CP}	3	A
Base Current		I_B	300	mA
Collector Power Dissipation		P_C *	0.9	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ 150	℃

* Package mounted on a ceramic board (600㎟ × 0.8㎜)

Marking

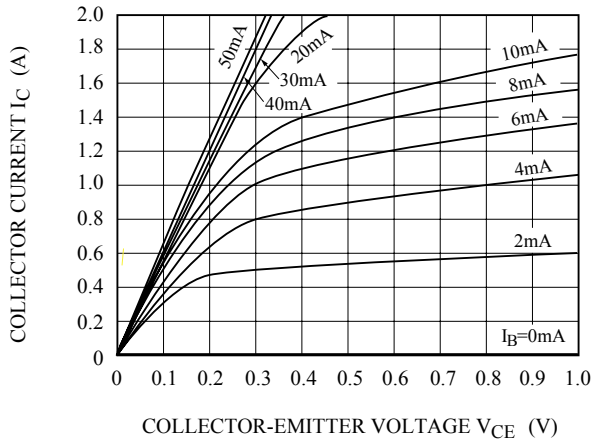


ELECTRICAL CHARACTERISTICS (Ta=25℃)

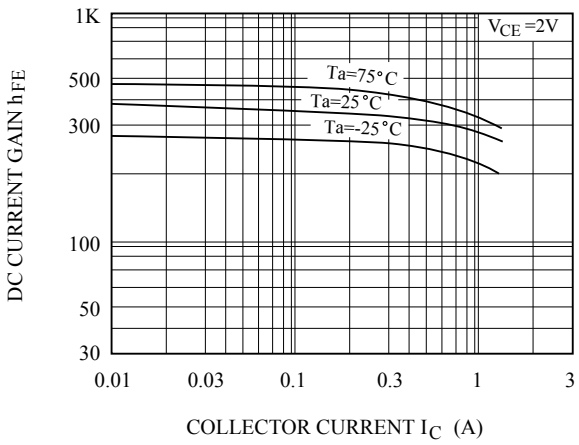
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=12V, I_E=0	-	-	0.1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=4V, I_C=0	-	-	0.1	μA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=10μA, I_E=0	20	-	-	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=1mA, I_B=0	20	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=10μA, I_C=0	5	-	-	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=750mA, I_B=15mA	-	130	200	mV
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=750mA, I_B=15mA	-	0.85	1.2	V
DC Current Gain		h_{FE}	V_{CE}=2V, I_C=100mA	200	-	560	
Transition Frequency		f_T	V_{CE}=2V, I_C=300mA	-	210	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, f=1MHz	-	20	-	pF
Swiitching Time	Turn-On Time	t_{on}		-	40	-	nS
	Storage Time	t_{stg}		-	180	-	
	Fall Time	t_f		-	20	-	

$20I_{B1}=-20I_{B2}=I_C=750mA$

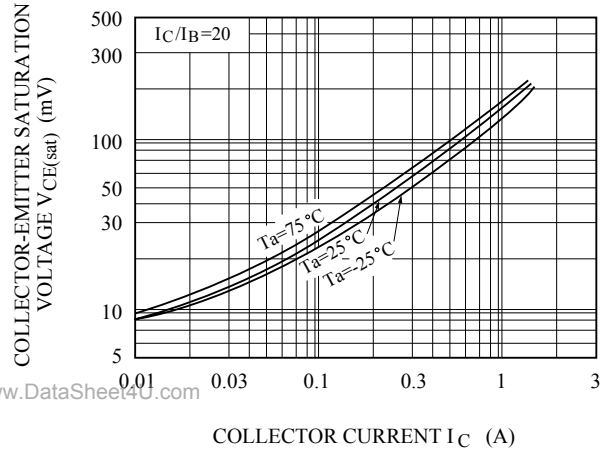
I_C - V_{CE}



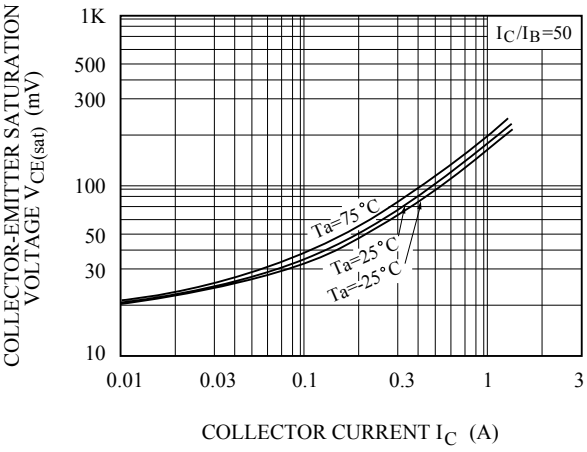
h_{FE} - I_C



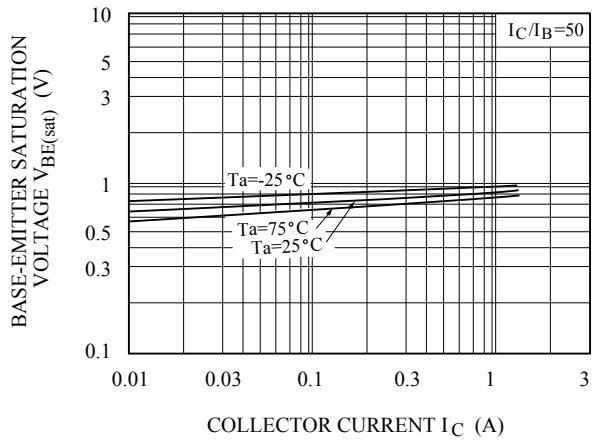
$V_{CE(sat)}$ - I_C



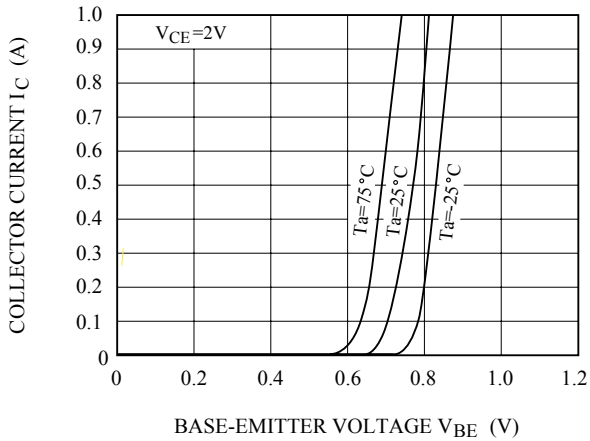
$V_{CE(sat)}$ - I_C



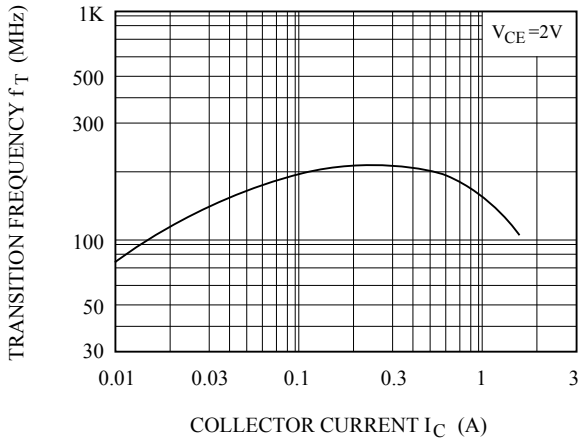
$V_{BE(sat)}$ - I_C



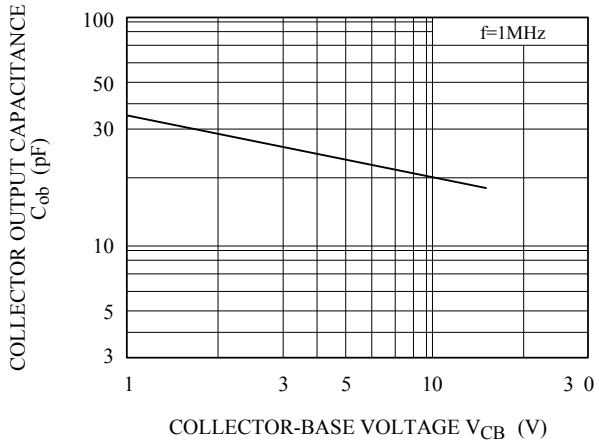
I_C - V_{BE}



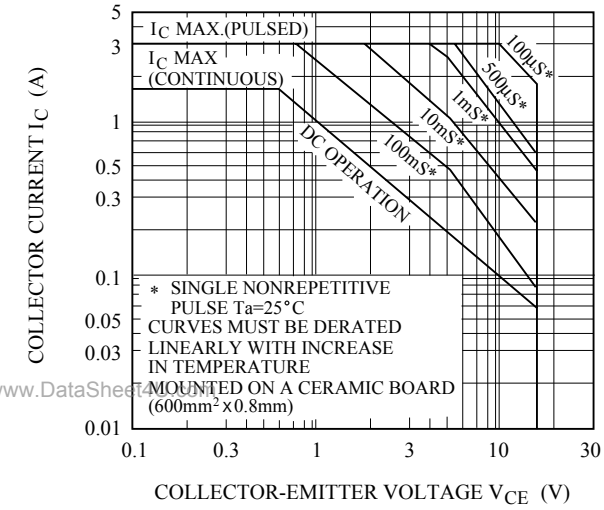
f_T - I_C



C_{ob} - V_{CB}



SAFE OPERATING AREA



Pc - Ta